

REMARKS

At the outset, Applicant wishes to thank the Examiner for the courtesies extended to the Applicant's representative during the telephone interview on May 19, 2004. The Office Action of April 20, 2004 has been received and contents carefully reviewed.

By this Amendment, Applicant amends claims 1, 11 and 23, and adds new claim 24. Claims 21-22 have been withdrawn as the result of the Examiner's constructive election in the Office Action dated October 27, 2003. Accordingly, claims 1, 3-7, 9-11 and 13-24 are currently pending in the present application. Reexamination and reconsideration of the application are respectfully requested.

In the Office Action, the Examiner rejected claims 1, 3-7, 9-11 and 13-20 under 35 U.S.C. § 112 ¶1; rejected claims rejected claim 23 under 35 U.S.C. § 102(b) as being anticipated by Applicant's Related Art ("ARA"), and rejected claims 1, 3-7, 9-11 and 13-20 under 35 U.S.C. § 103(a) as being unpatentable over ARA in view of Taniguchi et al. (JP 2-58030A). Applicant respectfully traverses this rejection.

With respect to the rejection under 35 U.S.C. § 112 ¶1, Applicant respectfully submits that in view of the current amendments in claims 1 and 11, this rejection is now believed to be moot, and that claims 1, 3-7, 9-11 and 13-20 are now in full compliance with 35 U.S.C. § 112 ¶1.

The rejection of claim 23 under 35 U.S.C. § 102(b) as being anticipated by ARA is respectfully traversed and reconsideration is requested.

Claim 23 is allowable over the cited references in that claim 23 recites a combination of elements including, for example, "a source electrode and a drain electrode on the semiconductor layer and adjacent the gate electrode, wherein the source electrode and the drain electrode oppose each other, each of the source electrode and drain electrode including at least one protrusion that extends toward the opposing electrode, and the protrusion of the source electrode is offset from the protrusion of the drain electrode... wherein the entirety of the protrusions of the source and drain electrodes is formed within the area of the semiconductor layer." None of the cited references, singly or in combination, teaches or suggests at least this feature of the

claimed invention. Accordingly, Applicant respectfully submits that claim 23 is allowable over the cited references.

The rejection of claims 1, 3-7, 9-11 and 13-20 under 35 U.S.C. § 103(a) as being unpatentable over ARA in view of Taniguchi et al. is respectfully traversed and reconsideration is requested.

Claim 1 is allowable over the cited references in that claim 1 recites a combination of elements including, for example, "...wherein an entire area of the "E"-shaped channel is formed over the gate electrode, the gate electrode underlies a part of the data line, the source electrodes and a part of the drain electrode so that the "E"-shaped channel is formed at parts of the source and drain electrodes facing the protrusion, the entirety of the protrusions of the source and drain electrodes is formed within the area of the semiconductor layer, and the protrusion of the source electrode is offset from the protrusion of the drain electrode." None of the cited references, singly or in combination, teaches or suggests at least this feature of the claimed invention. Accordingly, Applicant respectfully submits that claim 1 and claims 3-7 and 9-10, which depend therefrom, are allowable over the cited references.

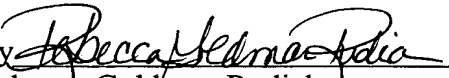
Claim 11 is allowable over the cited references in that claim 11 recites a combination of elements including, for example, "...wherein an entire area of the "E"-shaped channel is formed over the gate electrode, the gate electrode underlies a part of the data line, the source electrodes and a part of the drain electrode so that the "E"-shaped channel is formed at parts of the source and drain electrodes facing the protrusion, the entirety of the protrusions of the source and drain electrodes is formed within the area of the semiconductor layer, and the protrusion of the source electrode is offset from the protrusion of the drain electrode." None of the cited references, singly or in combination, teaches or suggests at least this feature of the claimed invention. Accordingly, Applicant respectfully submits that claim 11 and claims 13-20, which depend therefrom, are allowable over the cited references.

Applicant believes the foregoing amendments place the application in condition for allowance and early, favorable action is respectfully solicited. If the Examiner deems that a telephone conference would further the prosecution of this application, the Examiner is invited to call the undersigned attorney at the telephone number (202) 496-7500. All correspondence should continue to be sent to the below-listed address.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911.

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Respectfully submitted,

By 

Rebecca Goldman Rudich

Registration No.: 41,786

MCKENNA LONG & ALDRIDGE LLP

1900 K Street, N.W.

Washington, DC 20006

(202) 496-7500

Attorney for Applicant